

Data Sheet

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CMPFJ174
CMPFJ175
CMPFJ176
CMPFJ177

**SURFACE MOUNT
SILICON P-CHANNEL JFET**

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ174 Series types are epoxy molded P-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for low level amplifier applications.

Marking codes are 6V, 6W, 6X and 6Y respectively.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Gate-Drain Voltage	V _{GD}	30	V
Gate-Source Voltage	V _{GS}	30	V
Gate Current	I _G	50	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

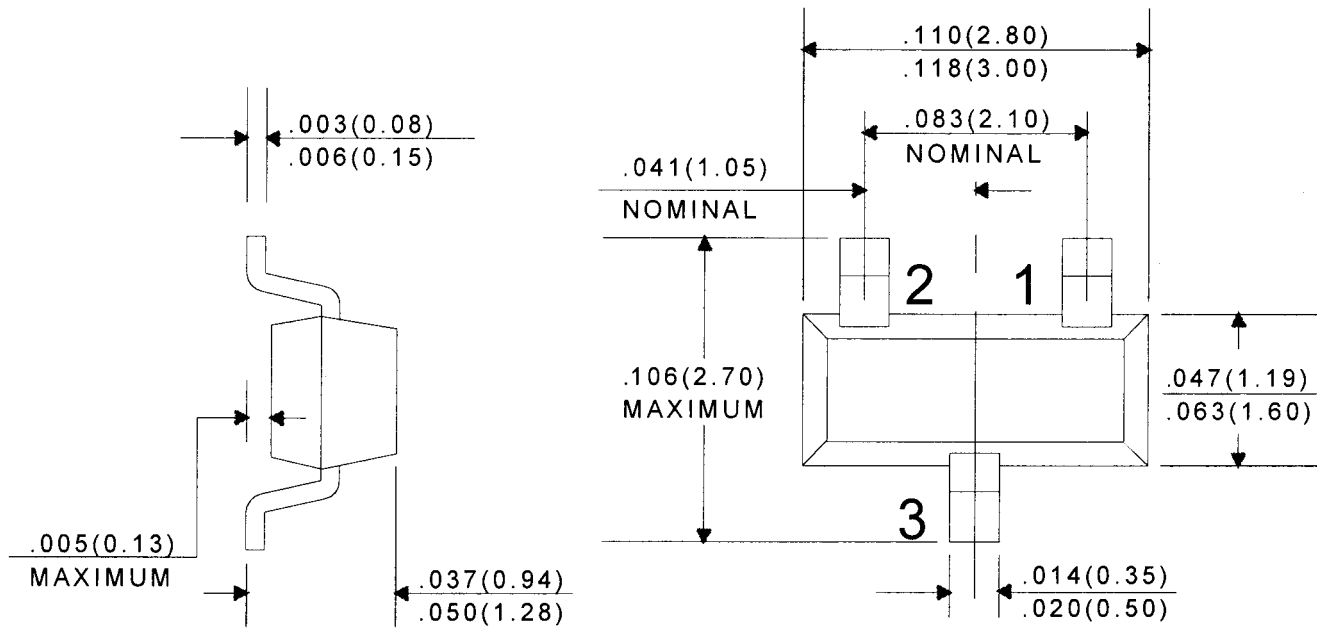
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPFJ174		CMPFJ175		CMPFJ176		CMPFJ177		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I _{GSS}	V _{GS} =20V		1.0		1.0		1.0		1.0	nA
I _{DSS}	V _{DS} =15V	20	100	7.0	60	2.0	25	1.5	20	mA
BV _{GSS}	I _G =1.0μA	30		30		30		30		V
V _{GS(off)}	V _{DS} =15V, I _D =10nA	5.0	10	3.0	6.0	1.0	4.0	0.8	2.5	V
r _{DS(ON)}	V _{DS} =0.1V		85		125		250		300	Ω

(SEE REVERSE SIDE)



SOT-23 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm)

LEAD CODE:

- 1) DRAIN
- 2) SOURCE
- 3) GATE

MARKING CODE:

CMPFJ174 - 6V
CMPFJ175 - 6W
CMPFJ176 - 6X
CMPFJ177 - 6Y

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